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Docket: 11811/US/2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

First Named Inventor:	Peter J. Schiller	
Application No.:	10/636,054	
Filing Date:	August 7, 2003	Examiner:
Title:	Solid-State Rotational Rate Sensor Device and Method	Group Art Unit: 2834

PRELIMINARY AMENDMENT

Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

I hereby certify that this document is being sent via First Class U.S. mail addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on this 20 day of August, 2004.

Barbara A. Avery
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Dear Sir:

Please amend the claims as follows:

1. (Currently Amended) A solid-state device having a thin-film piezoelectric material forming a plurality of piezoelectric elements on an integrated silicon chip, a first set of the plurality of piezoelectric elements generating a force, and a second set of the plurality of piezoelectric elements generating an electrical signal in proportion to both the force and a rate of rotation of the solid-state device while rejecting spurious noise.

2. (Currently Amended) A solid-state rotational rate sensor device, comprising:
an integrated silicon chip;

a first set of piezoelectric elements on the silicon chip;

a second set of piezoelectric elements on the silicon chip;

wherein the first set of piezoelectric elements including a piezoelectric material and being actuated by an electrical signal, wherein when the electrical signal is applied on the piezoelectric